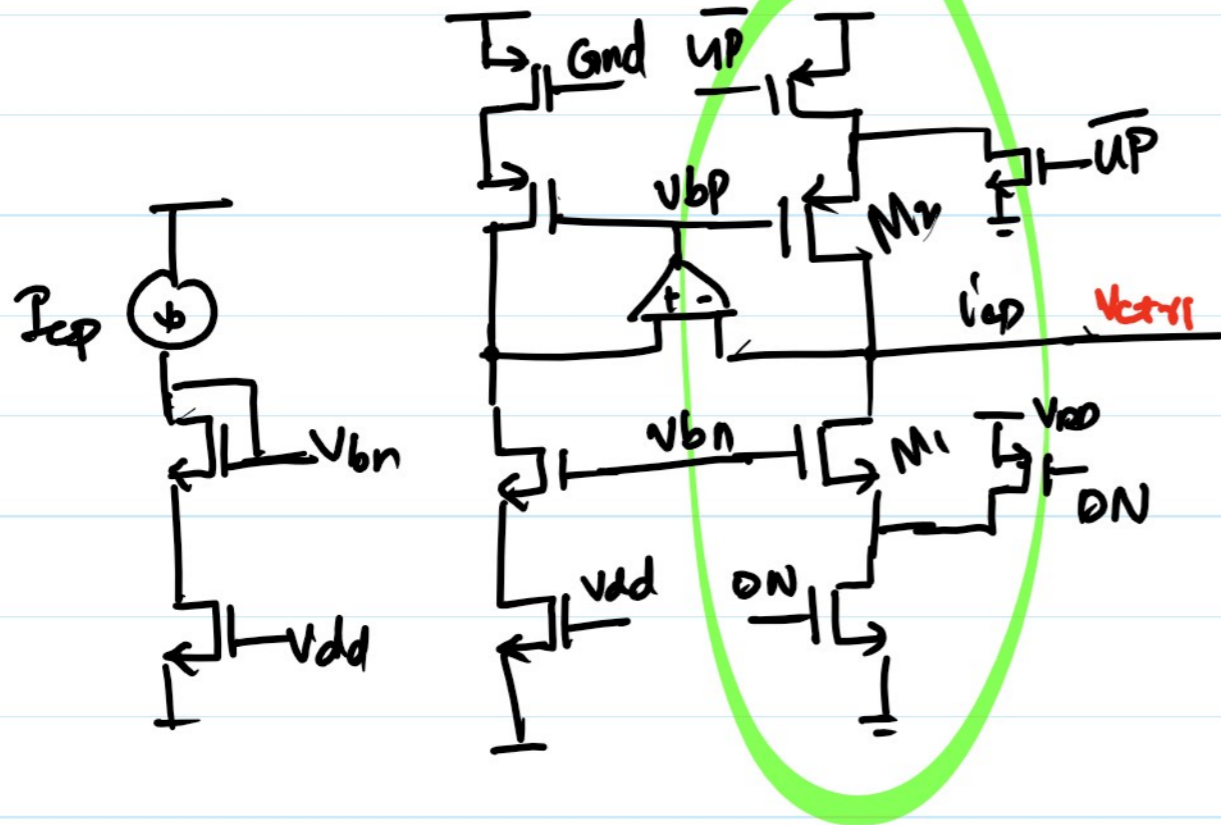


# Charge-pump.

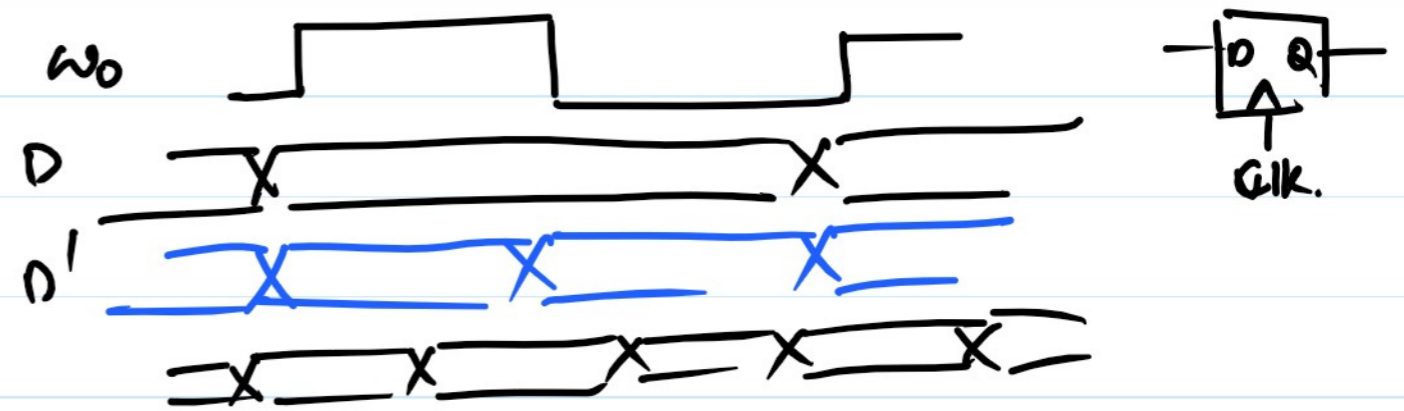
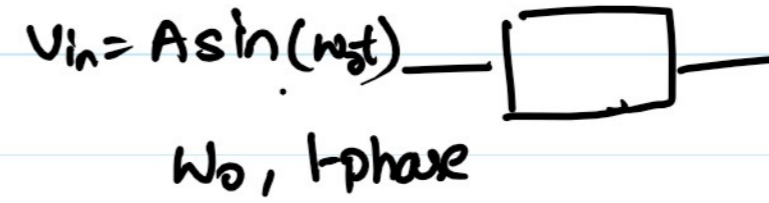
## Source-switched CP



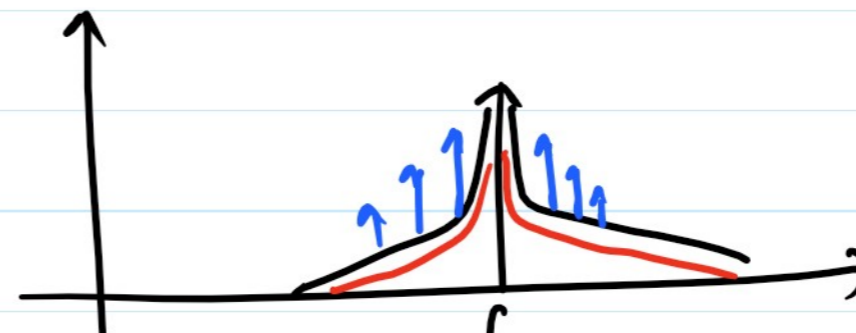
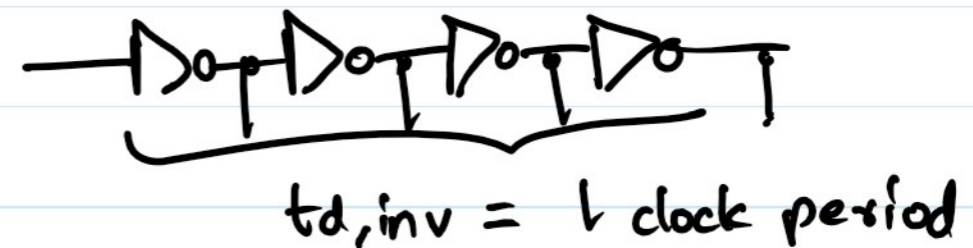
\* PMOS/NMOS current source switch between cutoff to saturation region.

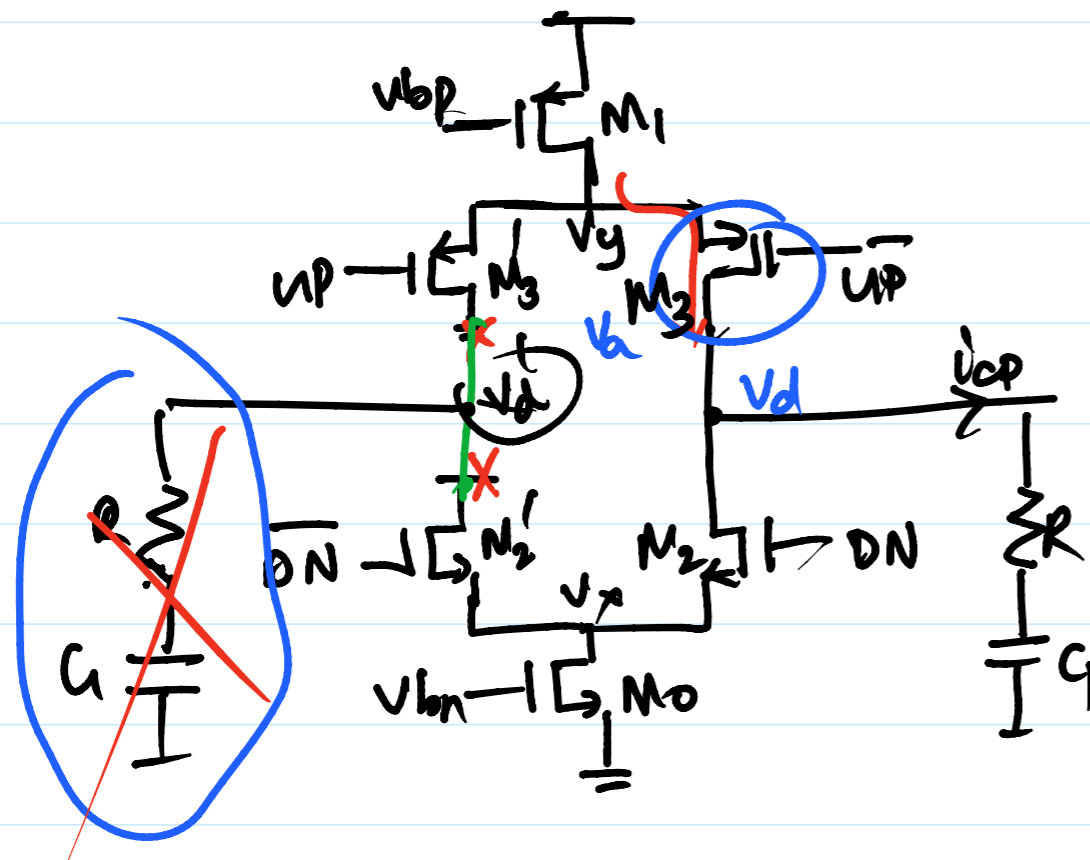
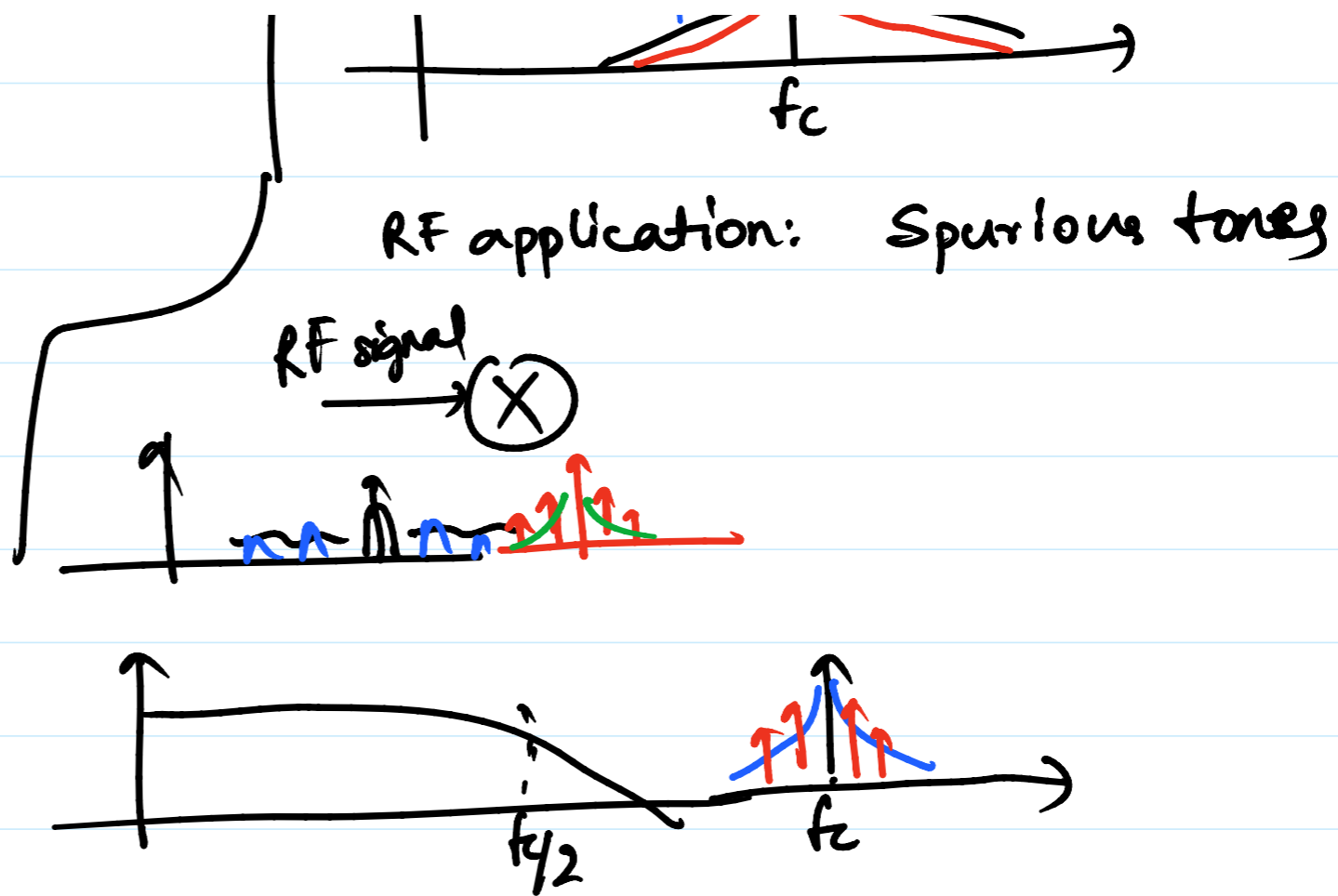
\* Ton mismatch between  $I_{up}$  &  $I_{dn}$ .

## Delay locked loop.



- Multi-phase clk required in sub-rate clock & data recovery

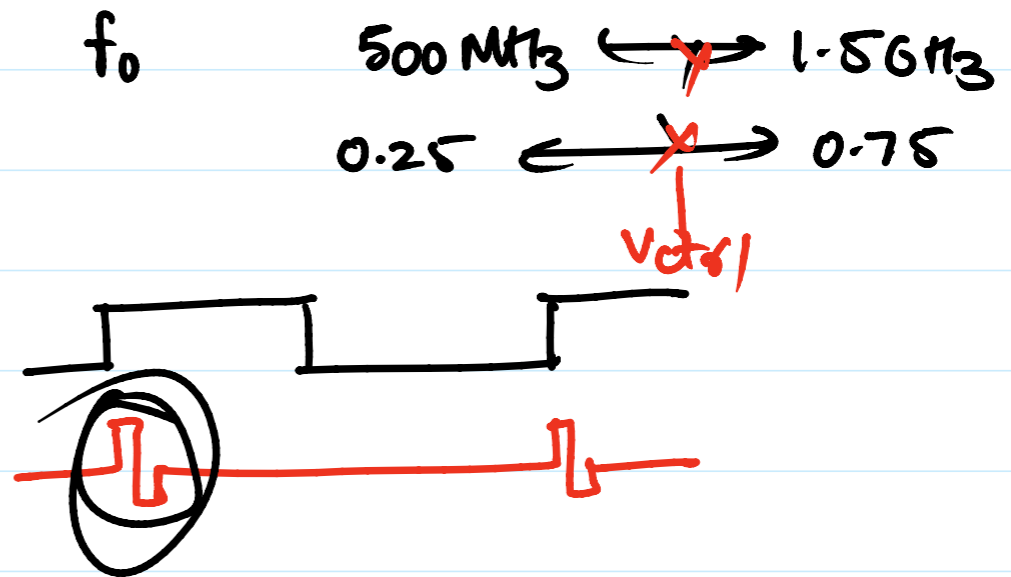
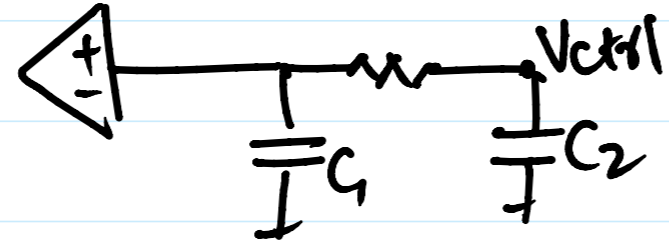
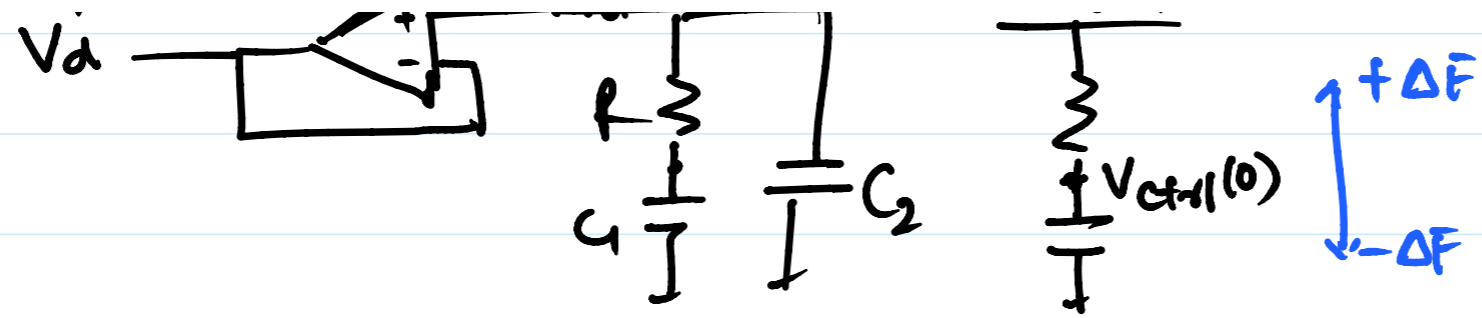




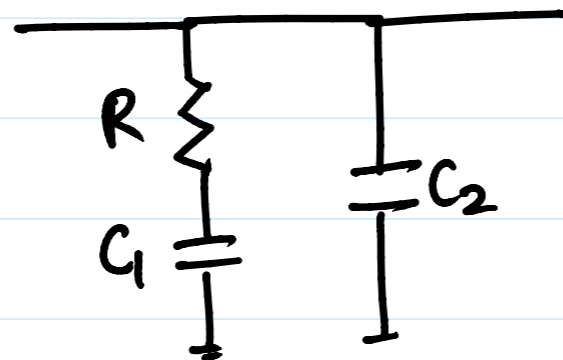
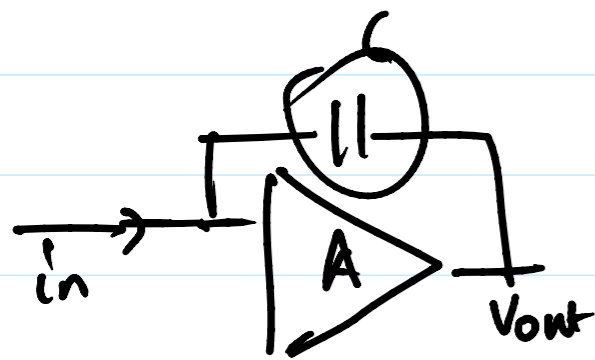
- $\times$  Current source is always ON.
- $\times$  Static-power consumption.
- $\checkmark$  Faster in switching.

- $\checkmark$  Transients on  $v_x/v_y$  are limited
- $\checkmark$  UP/DN signals can be limited swing
- $\times$  clock feed-through is a problem

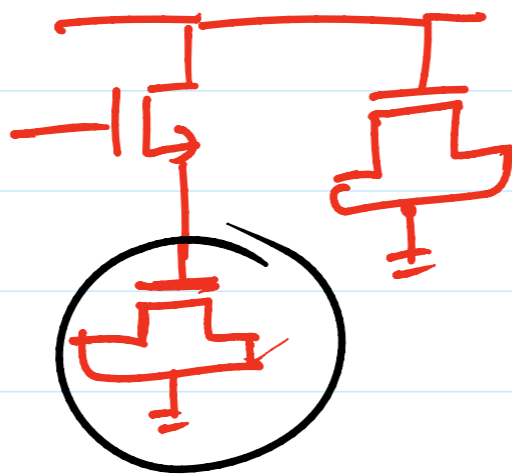




### Loop filter

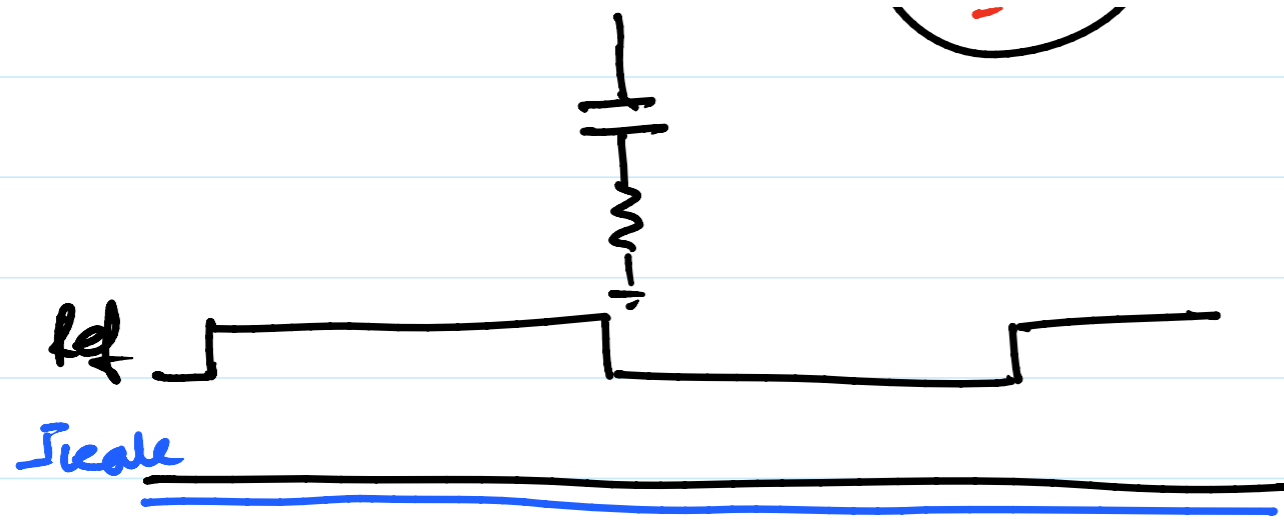


- \* Large phase margin  $\rightarrow$  large  $C_1$  loop F
- \* Resistor choice is based on noise



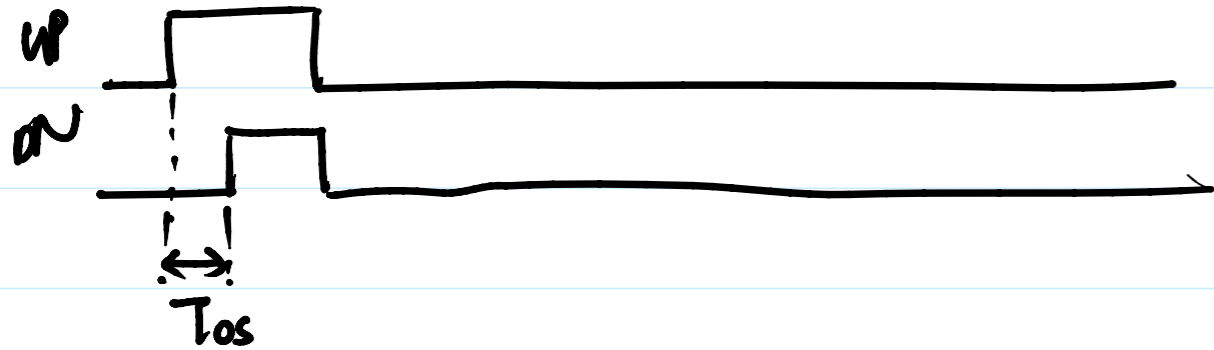
- \* Leak current in active devices
- \* Active MOS capacitance is dependent on control voltage.

I



$$I_{up} = I_{dn} = I_{cp}$$

$$I_{leak} \ll I_{cp}$$



$$I_{cp} \times \frac{T_{os}}{T_{ref}} = I_{leak}$$

$$T_{os} = \frac{I_{leak}}{I_{cp}} \cdot T_{ref}$$